



# BUK7M8R5-40H

N-channel 40 V, 8.5 mΩ standard level MOSFET in LPAK33

5 February 2019

Product data sheet

## 1. General description

Automotive qualified standard level N-channel MOSFET in an LPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

## 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
  - Low power losses, high power density
- LPAK copper clip package technology:
  - High robustness and reliability
  - Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

## 3. Applications

- 12 V automotive systems
- Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- DC-DC systems
- LED lighting

## 4. Quick reference data

Table 1. Quick reference data

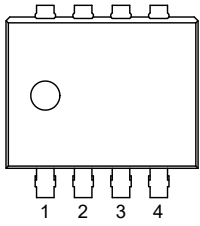
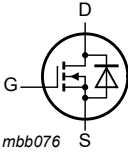
| Symbol                         | Parameter                        | Conditions                                                                                                                |     | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                |     | -   | -   | 40  | V    |
| $I_D$                          | drain current                    | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                 | [1] | -   | -   | 40  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                          |     | -   | -   | 59  | W    |
| <b>Static characteristics</b>  |                                  |                                                                                                                           |     |     |     |     |      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                             |     | 5.2 | 7.4 | 8.5 | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                           |     |     |     |     |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 15\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |     | -   | 2.6 | 5.2 | nC   |
| <b>Source-drain diode</b>      |                                  |                                                                                                                           |     |     |     |     |      |
| $Q_r$                          | recovered charge                 | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$              |     | -   | 15  | -   | nC   |

| Symbol | Parameter       | Conditions                                                                                                                                                | Min | Typ  | Max | Unit |
|--------|-----------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| S      | softness factor | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 17 | -   | 0.62 | -   |      |

[1] 40A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                         | Graphic symbol                                                                      |
|-----|--------|-----------------------------------|------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| 1   | S      | source                            |  <p>LFPAK33 (SOT1210)</p> |  |
| 2   | S      | source                            |                                                                                                            |                                                                                     |
| 3   | S      | source                            |                                                                                                            |                                                                                     |
| 4   | G      | gate                              |                                                                                                            |                                                                                     |
| mb  | D      | Mounting base; connected to drain |                                                                                                            |                                                                                     |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package |                                                                                 |         |
|--------------|---------|---------------------------------------------------------------------------------|---------|
|              | Name    | Description                                                                     | Version |
| BUK7M8R5-40H | LFPAK33 | Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch | SOT1210 |

## 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK7M8R5-40H | 78H040       |

## 8. Limiting values

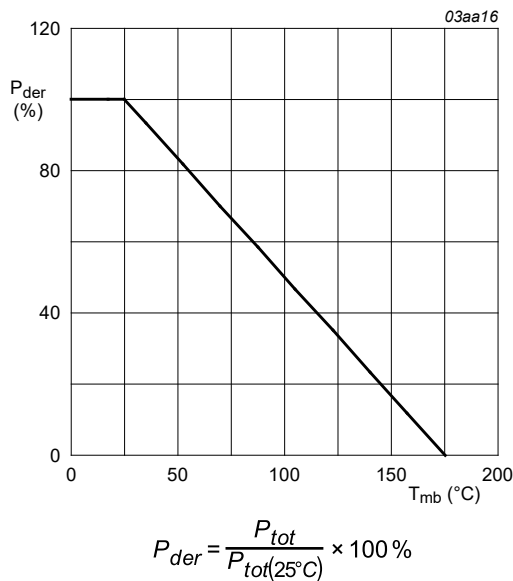
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

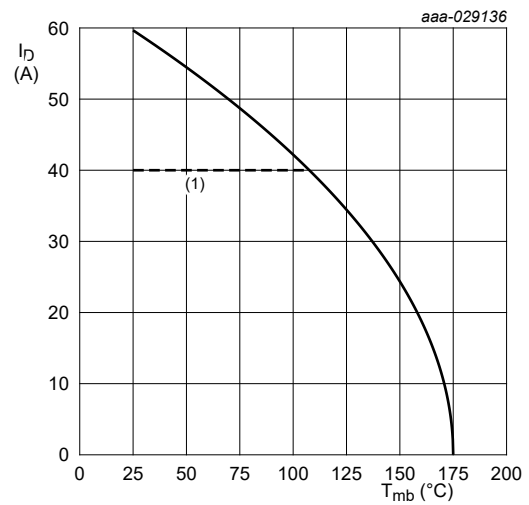
| Symbol             | Parameter               | Conditions                                                                              | Min | Max | Unit             |
|--------------------|-------------------------|-----------------------------------------------------------------------------------------|-----|-----|------------------|
| $V_{DS}$           | drain-source voltage    | $25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$                      | -   | 40  | V                |
| $V_{GS}$           | gate-source voltage     | DC; $T_j \leq 175\text{ }^\circ\text{C}$                                                | -10 | 20  | V                |
| $P_{tot}$          | total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ ; Fig. 1                                            | -   | 59  | W                |
| $I_D$              | drain current           | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; Fig. 2                   | [1] | 40  | A                |
|                    |                         | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^\circ\text{C}$ ; Fig. 2                  | -   | 40  | A                |
| $I_{DM}$           | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; Fig. 3 | -   | 239 | A                |
| $T_{stg}$          | storage temperature     |                                                                                         | -55 | 175 | $^\circ\text{C}$ |
| $T_j$              | junction temperature    |                                                                                         | -55 | 175 | $^\circ\text{C}$ |
| Source-drain diode |                         |                                                                                         |     |     |                  |

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                        |         | Min | Max | Unit |
|-----------------------------|----------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|-----|-----|------|
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$                                                                                                                                           |         | -   | 40  | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$                                                                                                |         | -   | 239 | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                   |         |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 40\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; unclamped; Fig. 4 | [2] [3] | -   | 24  | mJ   |

- [1] 40A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.  
 [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
 [3] Refer to application note AN10273 for further information.



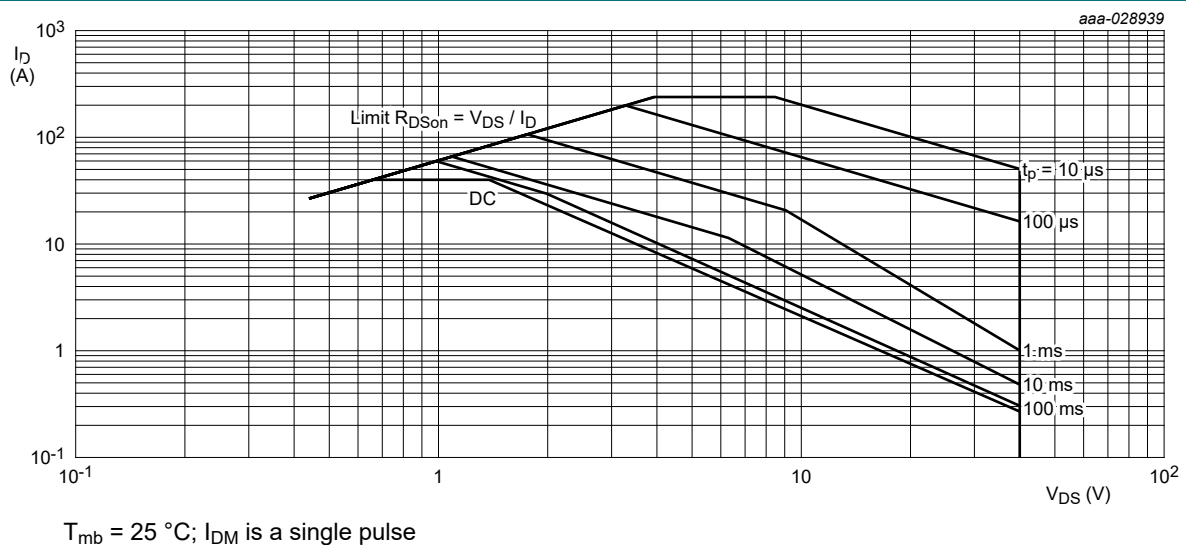
**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**



$V_{GS} \geq 10\text{ V}$

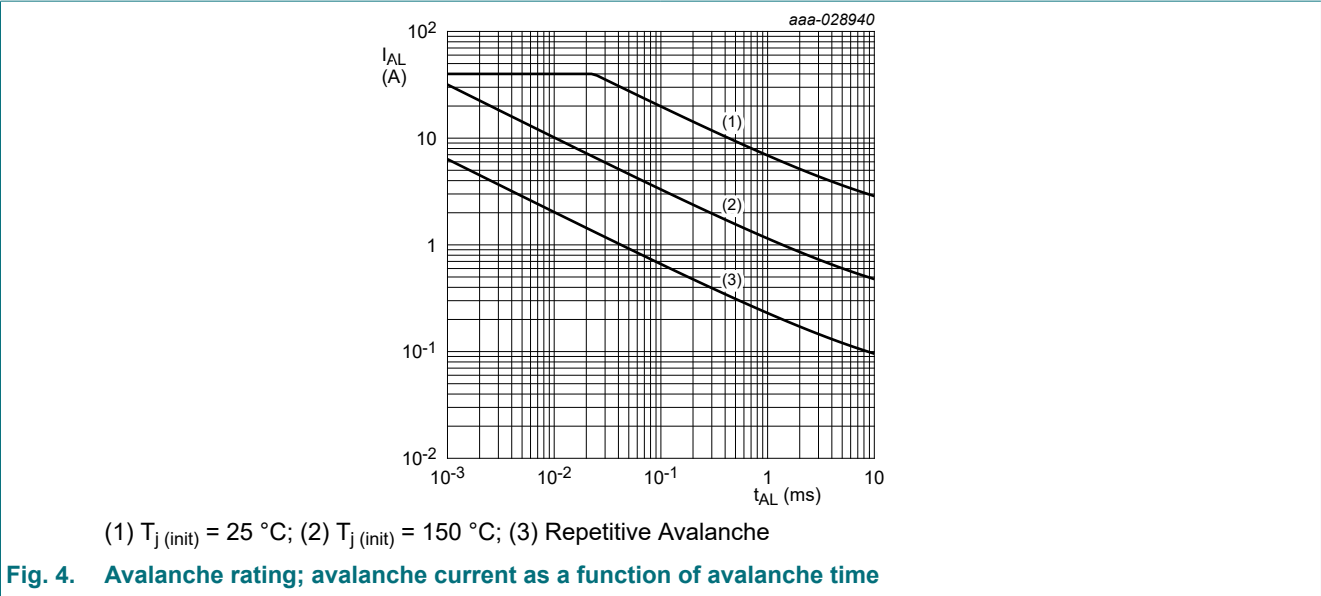
(1) 40A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2. Continuous drain current as a function of mounting base temperature**



$T_{mb} = 25\text{ °C}$ ;  $I_{DM}$  is a single pulse

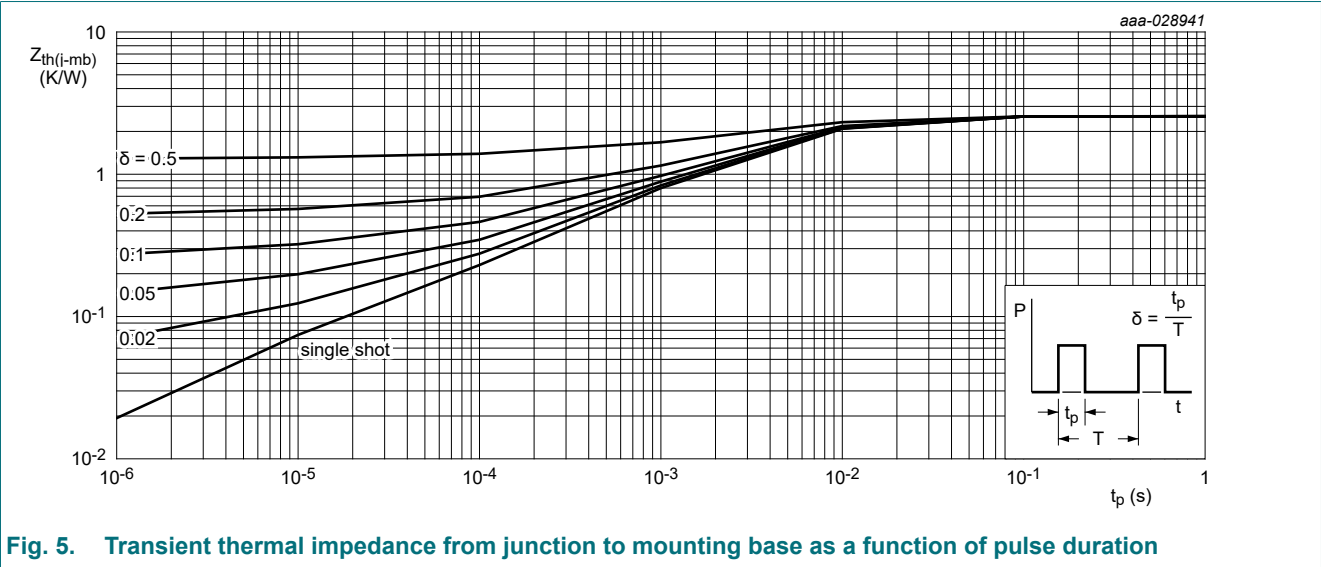
**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | 2.33 | 2.56 | K/W  |



10. Characteristics

Table 7. Characteristics

| Symbol                        | Parameter                      | Conditions                                                                     | Min | Typ  | Max | Unit |
|-------------------------------|--------------------------------|--------------------------------------------------------------------------------|-----|------|-----|------|
| <b>Static characteristics</b> |                                |                                                                                |     |      |     |      |
| $V_{(BR)DSS}$                 | drain-source breakdown voltage | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$  | 40  | 43   | -   | V    |
|                               |                                | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = -40\text{ °C}$ | -   | 40.5 | -   | V    |

## N-channel 40 V, 8.5 mΩ standard level MOSFET in LPAK33

| Symbol                  | Parameter                        | Conditions                                                                                                                                                                |  | Min | Typ  | Max  | Unit          |
|-------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|---------------|
|                         |                                  | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = -55\text{ }^\circ\text{C}$                                                                                |  | 36  | 40   | -    | V             |
| $V_{GS(th)}$            | gate-source threshold voltage    | $I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>                                               |  | 2.4 | 3    | 3.6  | V             |
|                         |                                  | $I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_J = -55\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                                       |  | -   | -    | 4.3  | V             |
|                         |                                  | $I_D = 1\text{ mA}$ ; $V_{DS}=V_{GS}$ ; $T_J = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                                       |  | 1   | -    | -    | V             |
| $I_{DSS}$               | drain leakage current            | $V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                                                                                         |  | -   | 0.05 | 1    | $\mu\text{A}$ |
|                         |                                  | $V_{DS} = 16\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$                                                                                        |  | -   | 0.42 | 10   | $\mu\text{A}$ |
|                         |                                  | $V_{DS} = 40\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 175\text{ }^\circ\text{C}$                                                                                        |  | -   | 36   | 500  | $\mu\text{A}$ |
| $I_{GSS}$               | gate leakage current             | $V_{GS} = 20\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                                                                                         |  | -   | 2    | 100  | nA            |
|                         |                                  | $V_{GS} = -10\text{ V}$ ; $V_{DS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$                                                                                        |  | -   | 2    | 100  | nA            |
| $R_{DSon}$              | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                                                                 |  | 5.2 | 7.4  | 8.5  | m $\Omega$    |
|                         |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_J = 105\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                                                                |  | 7.1 | 10.7 | 12.8 | m $\Omega$    |
|                         |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                                                                |  | 7.8 | 11.6 | 13.7 | m $\Omega$    |
|                         |                                  | $V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_J = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>                                                                |  | 9.5 | 13.9 | 16.5 | m $\Omega$    |
| $R_G$                   | gate resistance                  | $f = 1\text{ MHz}$ ; $T_J = 25\text{ }^\circ\text{C}$                                                                                                                     |  | 0.3 | 0.8  | 2    | $\Omega$      |
| Dynamic characteristics |                                  |                                                                                                                                                                           |  |     |      |      |               |
| $Q_{G(tot)}$            | total gate charge                | $I_D = 15\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>                                                 |  | -   | 14   | 20   | nC            |
| $Q_{GS}$                | gate-source charge               |                                                                                                                                                                           |  | -   | 4.5  | 6.8  | nC            |
| $Q_{GD}$                | gate-drain charge                |                                                                                                                                                                           |  | -   | 2.6  | 5.2  | nC            |
| $C_{iss}$               | input capacitance                | $V_{DS} = 25\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 15</a>                                          |  | -   | 935  | 1309 | pF            |
| $C_{oss}$               | output capacitance               |                                                                                                                                                                           |  | -   | 374  | 524  | pF            |
| $C_{rss}$               | reverse transfer capacitance     |                                                                                                                                                                           |  | -   | 43   | 95   | pF            |
| $t_{d(on)}$             | turn-on delay time               | $V_{DS} = 30\text{ V}$ ; $R_L = 2\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $R_{G(ext)} = 5\text{ }\Omega$                                                                |  | -   | 5    | -    | ns            |
| $t_r$                   | rise time                        |                                                                                                                                                                           |  | -   | 3.2  | -    | ns            |
| $t_{d(off)}$            | turn-off delay time              |                                                                                                                                                                           |  | -   | 9.2  | -    | ns            |
| $t_f$                   | fall time                        |                                                                                                                                                                           |  | -   | 3.7  | -    | ns            |
| Source-drain diode      |                                  |                                                                                                                                                                           |  |     |      |      |               |
| $V_{SD}$                | source-drain voltage             | $I_S = 15\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>                                                                  |  | -   | 0.85 | 1.2  | V             |
| $t_{rr}$                | reverse recovery time            | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 17</a>                                    |  | -   | 22   | -    | ns            |
| $Q_r$                   | recovered charge                 | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$                                                              |  | -   | 15   | -    | nC            |
| S                       | softness factor                  | $I_S = 15\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a> |  | -   | 0.62 | -    |               |
|                         |                                  | $I_S = 15\text{ A}$ ; $dI_S/dt = -500\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a> |  | -   | 0.42 | -    |               |

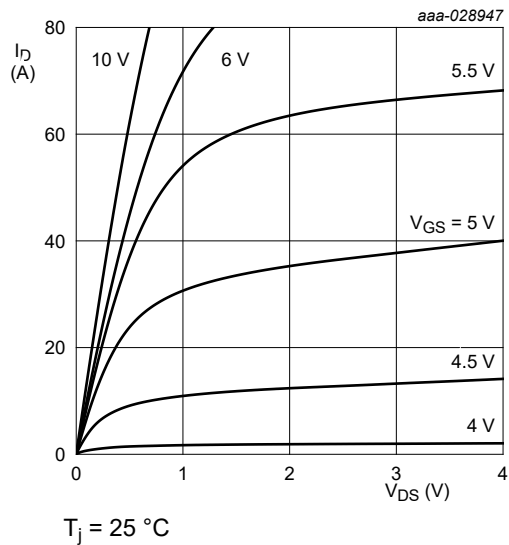


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

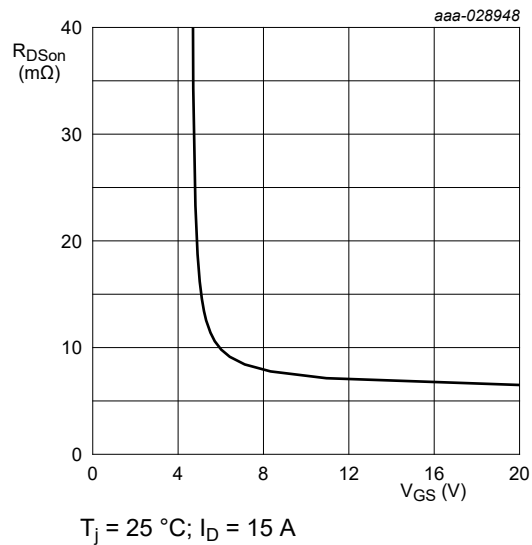


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

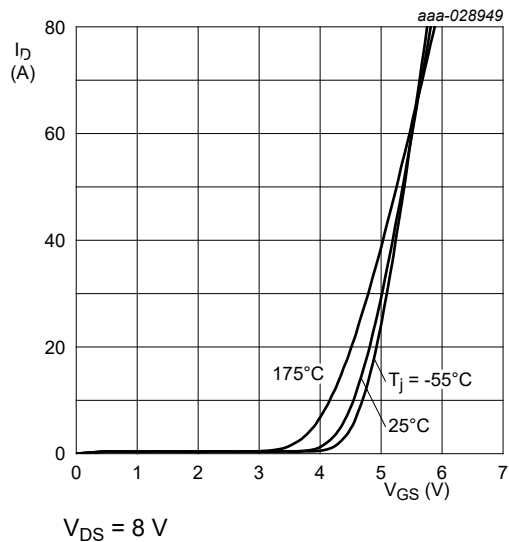


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

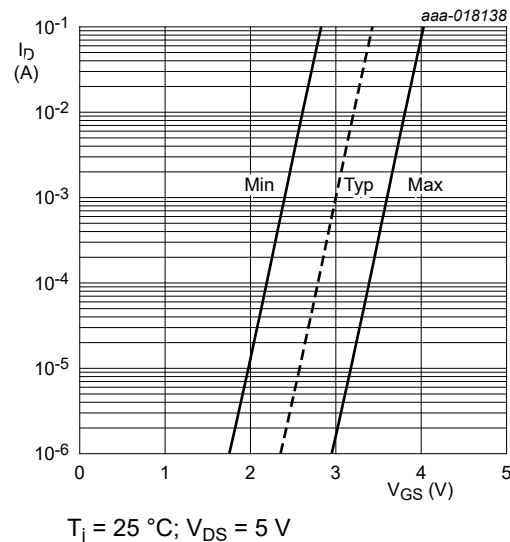


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

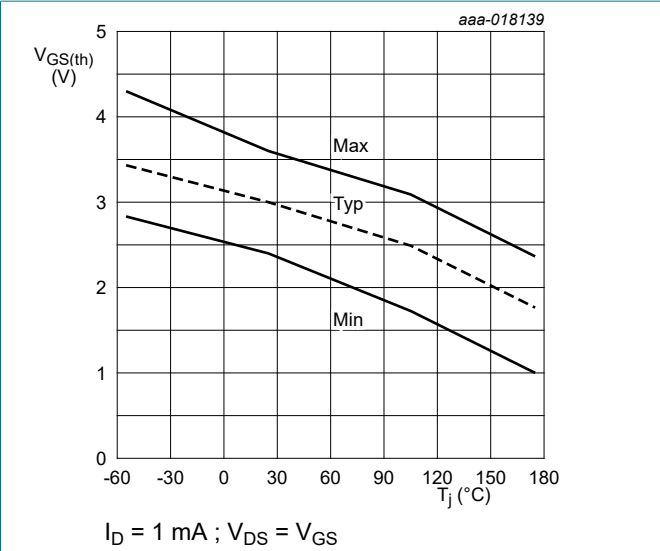


Fig. 10. Gate-source threshold voltage as a function of junction temperature

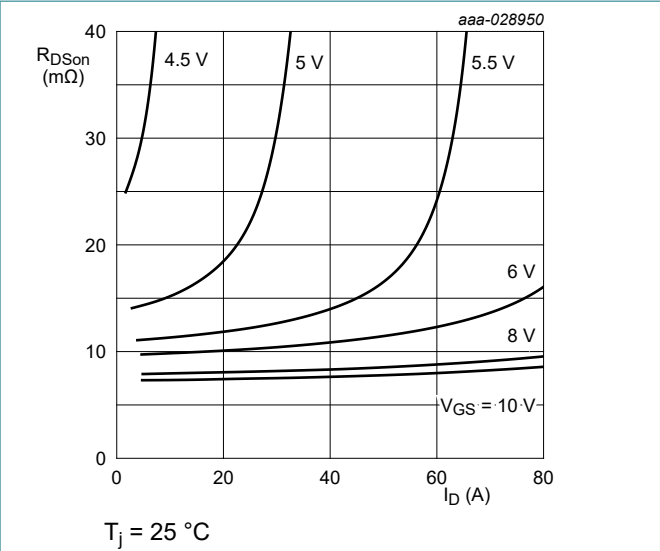


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

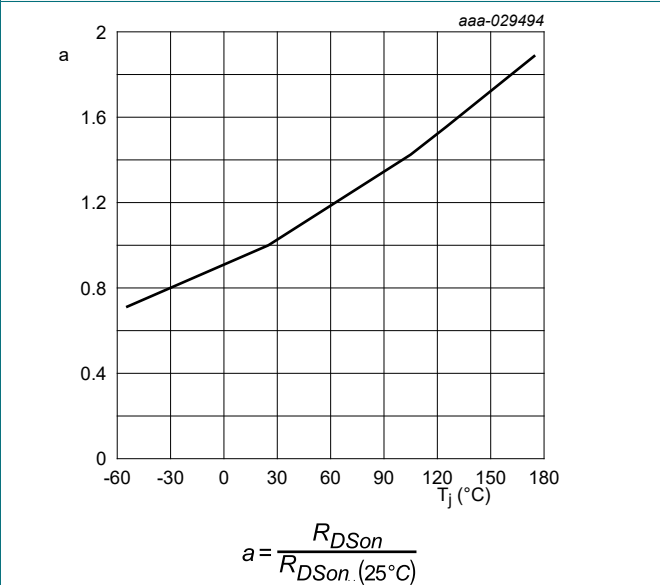


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

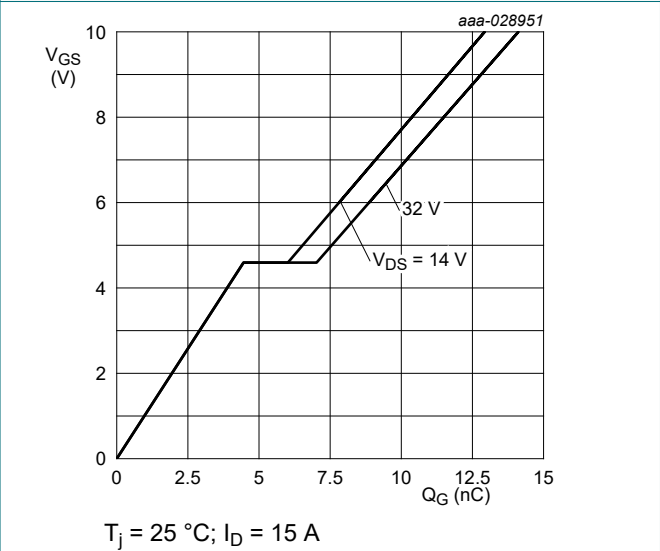


Fig. 13. Gate-source voltage as a function of gate charge; typical values

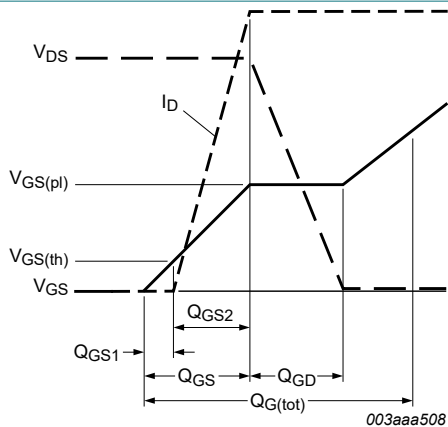
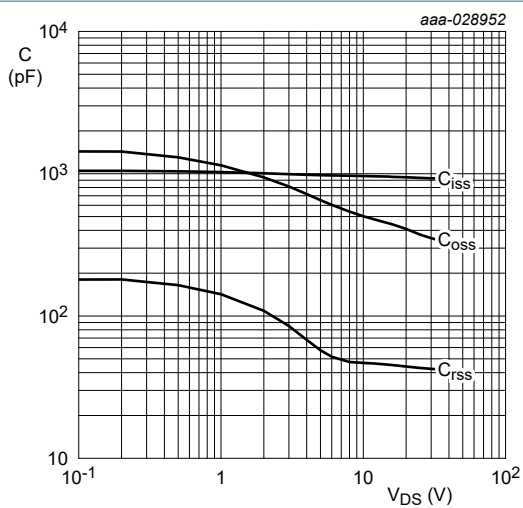
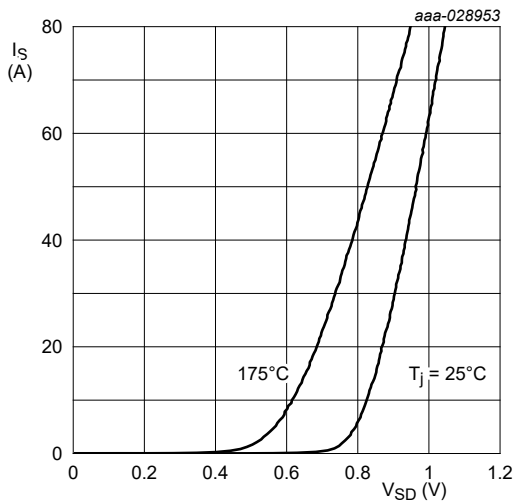


Fig. 14. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0 \text{ V}$

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

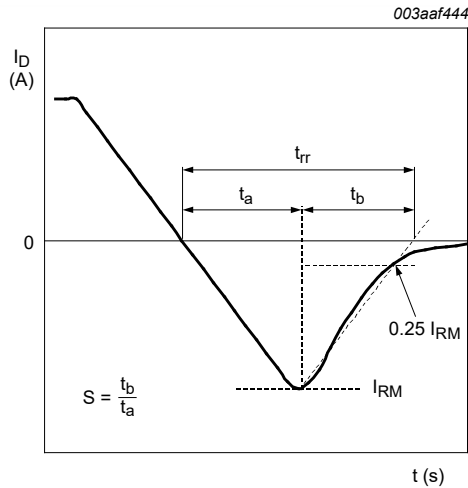


Fig. 17. Reverse recovery timing definition



11. Package outline

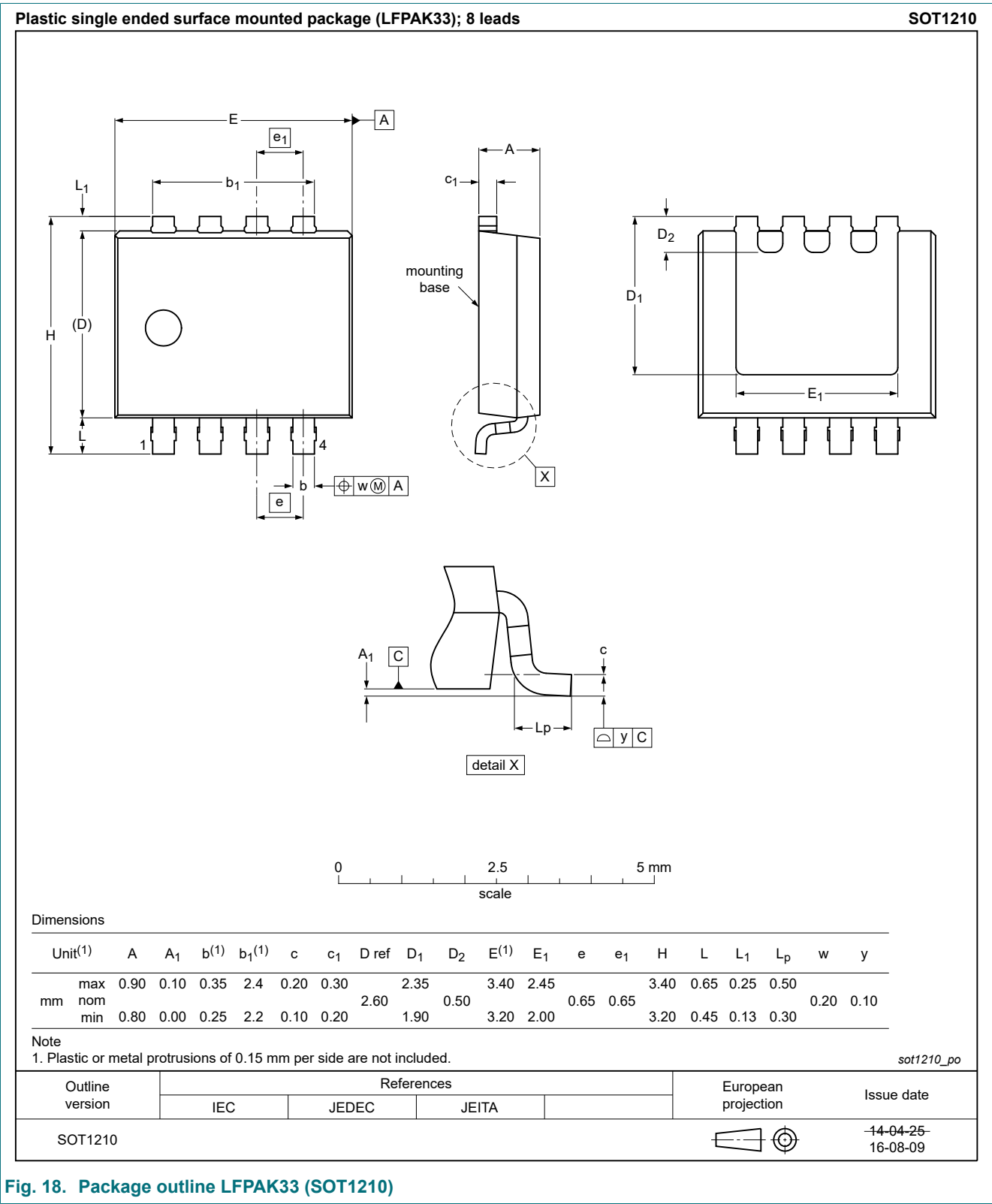


Fig. 18. Package outline LPAK33 (SOT1210)

## 12. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
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